

RF POWER TRANSISTOR

DESCRIPTION:

The **ASI 1214-6** is a Common Base Transistor Designed for Long Pulse High Reliability L-Band Radar Applications.

FEATURES INCLUDE:

- Gold Metallization
- Hermetic Package
- Input/Output Matching

MAXIMUM RATINGS

I_C	5.0 A
V_{CB}	55 V
P_{DISS}	125 W @ T _C = 25 °C
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +200 °C
θ_{JC}	1.4 °C/W

PACKAGE - .400 x .400 2NLFL

	MINIMUM Inches/mm	MAXIMUM Inches/mm		MINIMUM Inches/mm	MAXIMUM Inches/mm
		055/1.40	K	002/0.05	006/0.15
B	120/3.05	130/3.30	L	055/1.40	065/1.65
C		785/19.94	M	080/2.03	095/2.41
D	455/11.56	465/11.81	N		195/4.93
E	130/3.30		P	455/11.56	468/11.89
F	236/5.84				
G	108/3.25				
H	838/21.28	850/21.59			
I	1095/27.81	1105/28.07			
J	525/13.34	535/13.59			

1 = COLLECTOR
 3 = EMITTER 2 & 4 = BASE

CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CBO}	I _C = 20 mA	55			V
BV_{CER}	I _C = 40 mA R _{BE} = 10 Ω	55			V
BV_{EBO}	I _E = 2.0 mA	3.5			V
I_{CES}	V _{CE} = 28 V			10	mA
h_{FE}	V _{CE} = 5.0 V I _C = 2.0 A	15		150	---
P_G	V _{CC} = 28 V P _{OUT} = 55 W f = 1214 to 1400 MHz	6.6	7.2		dB
η_C	Pulse Width = 1000 μS Duty Cycle = 10%	50	55		%